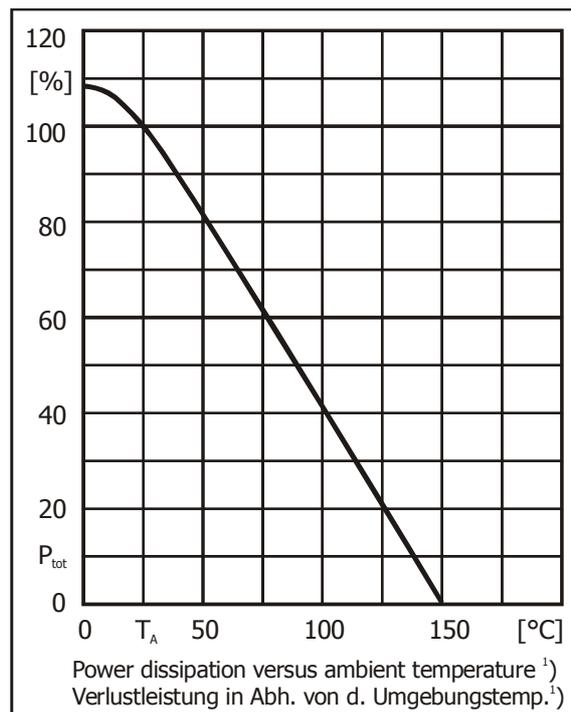


Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
Emitter-Base cutoff current – Emitter-Basis-Reststrom - V _{EB} = 4 V, (C open)	- I _{EB0}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz - I _C = 100 mA, - V _{CE} = 1 V, f = 100 MHz	f _T	50 MHz	–	–
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R _{thA}	< 200 K/W ¹⁾		
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren		MPSA06		



1 Valid, if leads are kept at ambient temperature at a distance of 2 mm from case
 Gültig wenn die Anschlussdrähte in 2 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden